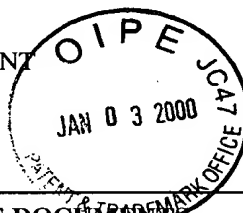


37 CFR 1.501  
 INFORMATION DISCLOSURE STATEMENT  
 IN A PATENT  
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Docket No. <b>P97,0027</b>	Serial No. <b>08/818,239</b>
Applicant <b>Hiroshi Tayanaka</b>	
Filing Date <b>March 14, 1997</b>	Group Art Unit <b>2813</b>

## U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If appropriate
<i>LC</i>	AA	4,727,047	02-23-88	Bozler, et al.	—	—	
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							Yes	No
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<i>LC</i>	AT	V. Labunov, et al., "Heat Treatment Effect on Porous Silicon", Thin Solid Films, Vol. 137, pp. 123-134, 1986
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<i>LC</i>	AV	"Crystalline Silicon and Doping", Maruzen Kabushiki Kaisha Publisher, 1986
	AW	
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no translation  
 no explanation

Examiner *LC Clinton*

Date Considered *6/5/2000*

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.